# MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

## ABSTRACT

A manufacturing method of a semiconductor device includes preparing a semiconductor substrate which is a base substrate of the semiconductor device and which is formed with a concavity and convexity part on the surface of the semiconductor substrate. The method further comprises depositing on the surface of the semiconductor substrate an impurity thin film including an impurity atom which becomes a donor or an acceptor in the semiconductor substrate and performing an ion implantation from a diagonal upper direction to the impurity thin film deposited on the concavity and convexity part of the semiconductor substrate. The method still further comprises recoiling the impurity atom from the inside of the impurity thin film to the inside of the concavity and convexity part by performing the ion implantation.

FIG. 2A-2D